

### 1. Product Name

Photo diode chip DD3-30

### 2. Absolute Maximum Ratings

Ta=25°C

Parameter	Symbol	Rating	Unit.
Reverse voltage	VR	15	V

### 3. Electro-Optical Characteristics

Ta=25°C

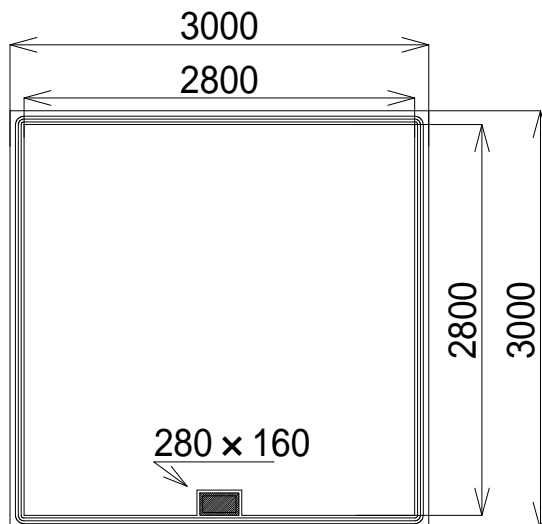
Parameter	Symbol	Condition	Min	Typ	Max	Unit.
Dark current	Id	VR=10V			20	nA
Spectral sensitivity	$\lambda$		450 ~ 1050			nm
Peak sensitivity wavelength	$\lambda p$			920		nm
Terminal capacitance	Ct	VR=0V f=1MHz		94		pF

### 4. Dimension (Unit: $\mu\text{m}$ )

Chip size ※1	$\square 3000 \mu\text{m}$
Chip thickness	$280 \pm 15 \mu\text{m}$
Active area	$\square 2800 \mu\text{m}$

※1 The size after the dicing is  $\square 2960 \mu\text{m}$ .

Passivation	SiN
Fore side electrode	$\langle \text{Anode} \rangle \text{Al}$
Back side electrode	$\langle \text{Cathode} \rangle \text{Au}$
Wafer size	6inch



The contents of this data sheet are subject to change without advance notice for the purpose of improvement. When using this product, would you please refer to the latest specifications.